Quad 2-Input NAND Schmitt Trigger

MC74LVX132

The MC74LVX132 is an advanced high speed CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology.

Pin configuration and function are the same as the MC74LVX00, but the inputs have hysteresis.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 6.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: t_{PD} = 5.8 ns (Typ) at V_{CC} = 3.3 V
- Low Power Dissipation: I_{CC} = 2 μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Low Noise: V_{OLP} = 0.5 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V
- These Devices are Pb−Free and are RoHS Compliant

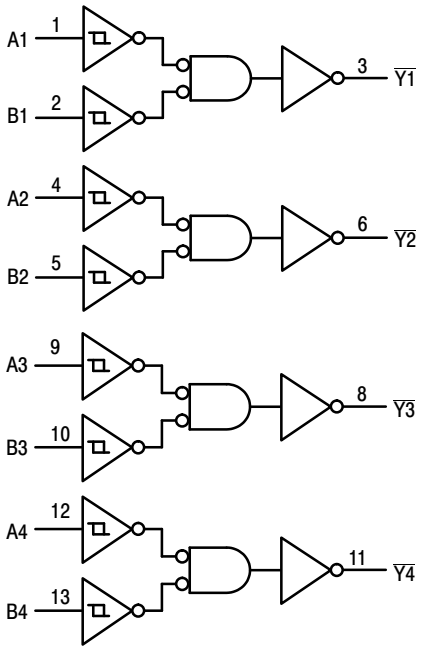


Figure 1. Logic Diagram

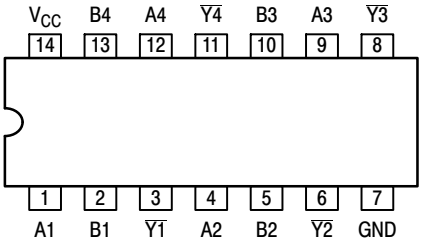
FUNCTION TABLE

A Input	B Input	$\overline{Y}$ Output
L	L	H
L	H	H
H	L	H
H	H	L

SOIC−14 NB
D SUFFIX
CASE 751A

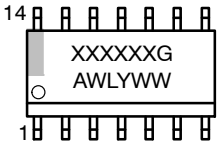
TSSOP−14
DT SUFFIX
CASE 948G

PIN ASSIGNMENT

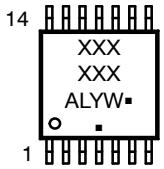


14−Lead (Top View)

MARKING DIAGRAMS



SOIC−14 NB



TSSOP−14

XXX = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_{IN}	DC Input Voltage		−0.5 to +6.5	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current	V_I < GND	−20	mA
I_{OK}	DC Output Diode Current	V_O < GND	±20	mA
I_{OUT}	DC Output Sink Current		±25	mA
I_{CC}	DC Supply Current per Supply Pin		±50	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	116 150	°C/W
P_D	Power Dissipation in Still Air at 25°C	SOIC TSSOP	1077 833	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating Oxygen Index: 30% − 35%		UL 94−V0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Charged Device Model (Note 2)	> 2000 N/A	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 3)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22−A114−A.
2. Tested to JESD22−C101−A.
3. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage		2.0	3.6	V
V_I	Input Voltage	(Note 4)	0	5.5	V
V_O	Output Voltage	(HIGH or LOW State)	0	5.5	V
T_A	Operating Free−Air Temperature		−40	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 3.0 V ±0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs may not be left open. All inputs must be tied to a high− or low−logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	T_A = 25°C			T_A = ≤ 85°C		T_A = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{T+}	Positive Threshold Voltage (Figure 4)		2.0 3.0 3.6	1.15 1.50 1.70	1.31 1.82 2.12	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	1.15 1.50 1.70	1.60 2.25 2.60	V
V_{T-}	Negative Threshold Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.75 1.00	0.64 1.13 1.46	0.9 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	0.30 0.75 1.00	0.90 1.45 1.90	V
V_H	Hysteresis Voltage (Figure 4)		2.0 3.0 3.6	0.30 0.30 0.35	0.70 0.76 0.69	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	0.30 0.30 0.35	1.30 1.50 1.60	V
V_{OH}	Minimum High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OH} = − 50 μA I_{OH} = − 50 μA I_{OH} = − 4 mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		1.9 2.9 2.34		V
V_{OL}	Maximum Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OL} = 50 μA I_{OL} = 50 μA I_{OL} = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44		0.1 0.1 0.52	V
I_{in}	Maximum Input Leakage Current	V_{in} = 5.5 V or GND	3.6			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{in} = V_{CC} or GND	3.6			2.0		20		20	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

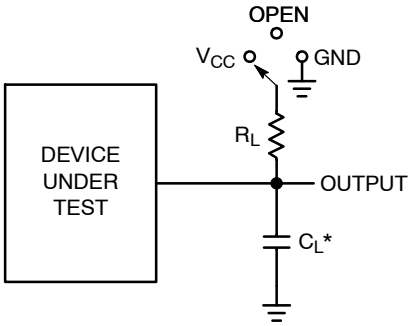
AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions		T_A = 25°C			T_A = ≤ 85°C		T_A = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, A or B to $\overline{Y}$	V_{CC} = 2.7V	C_L = 15pF C_L = 50pF		7.0 10.0	11.0 16.0	1.0 1.0	13.0 18.7	1.0 1.0	15.0 20.0	ns
		V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		5.8 8.3	10.6 15.4	1.0 1.0	12.5 17.5	1.0 1.0	14.5 19.5	
t_{OSHL}, t_{OSLH}	Output to Output Skew (Note 5)	V_{CC} = 2.7V	C_L = 50pF			1.5		1.5		1.5	ns
		V_{CC} = 3.3 ± 0.3V	C_L = 50pF			1.5		1.5		1.5	
C_{in}	Maximum Input Capacitance				4	10		10		10	pF
				Typical @ 25°C, V_{CC} = 5.0 V							
C_{PD}	Power Dissipation Capacitance (Note 5)			11							pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no−load dynamic power consumption; P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 5.0 V)

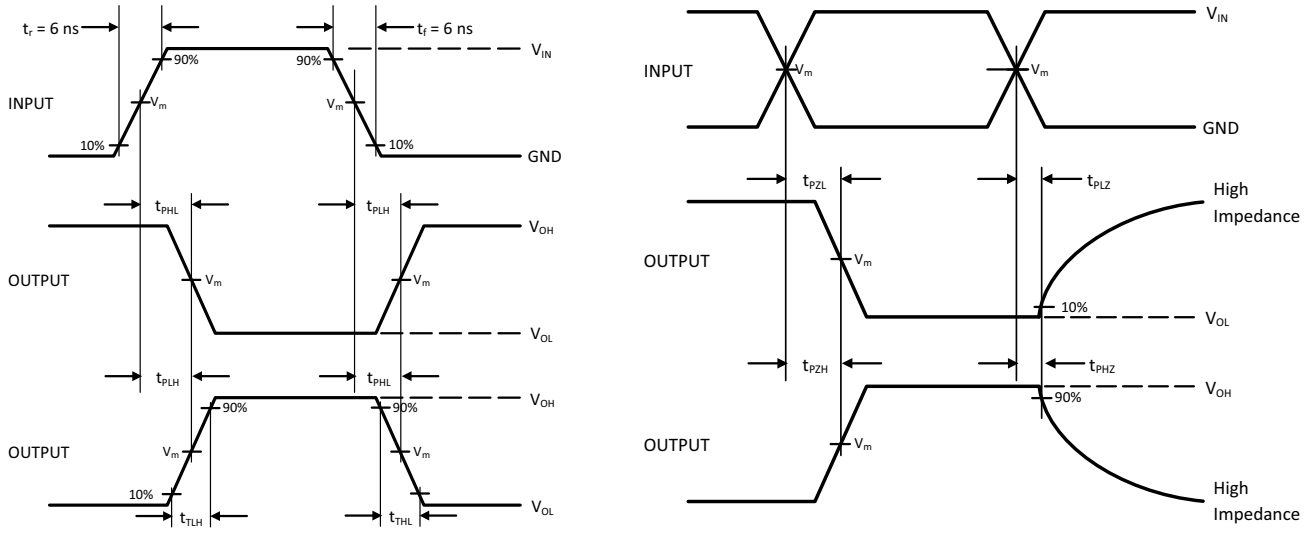
Symbol	Characteristic	T_A = 25°C		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.5	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.5	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V



*C_L Includes probe and jig capacitance

Test	Switch Position	C_L	R_L
t_{PLH} / t_{PHL}	Open	See AC Charac-terisitcs Table	1 kΩ
t_{PLZ} / t_{PZL}	V_{CC}		
t_{PHZ} / t_{PZH}	GND		

Figure 2. Test Circuit



Device	V_{IN}, V	V_m, V
MC74LVX132	V_{CC}	50% x V_{CC}

Figure 3. Switching Waveforms

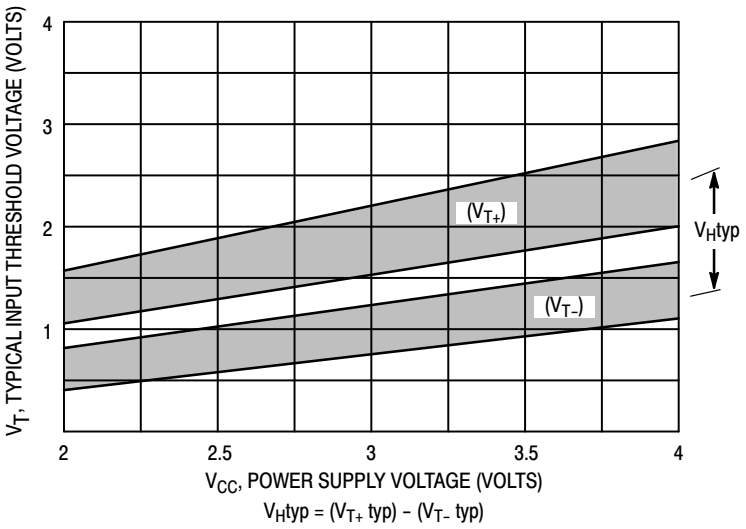
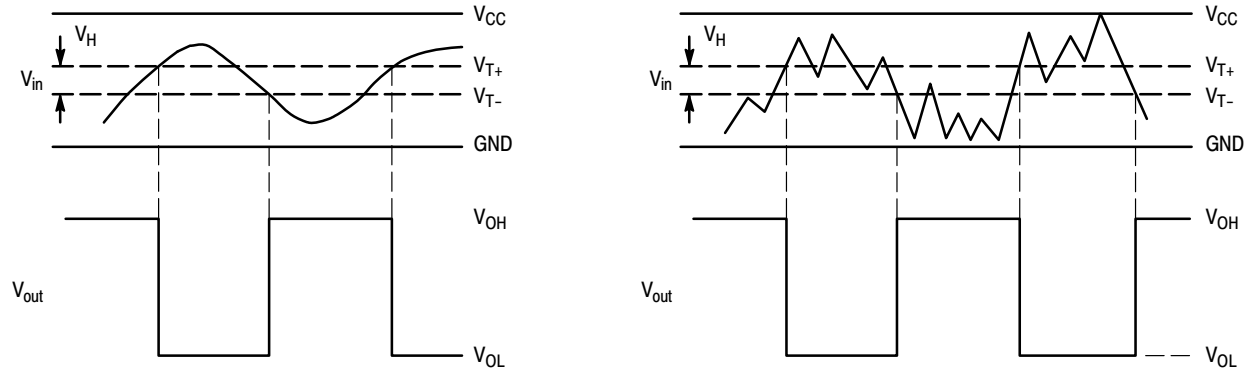


Figure 4. Typical Input Threshold, V_{T+}, V_{T-} versus Power Supply Voltage



(a) A Schmitt−Trigger Squares Up Inputs With Slow Rise and Fall Times

(b) A Schmitt−Trigger Offers Maximum Noise Immunity

Figure 5. Typical Schmitt−Trigger Applications

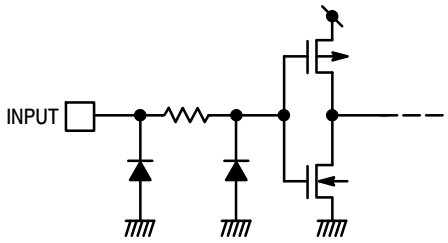


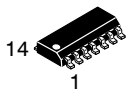
Figure 6. Input Equivalent Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping†
MC74LVX132DR2G	LVX132	SOIC−14	2500 Tape & Reel
MC74LVX132DTG	LVX 132	TSSOP−14	96 Units / Rail
MC74LVX132DTR2G	LVX 132	TSSOP−14	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

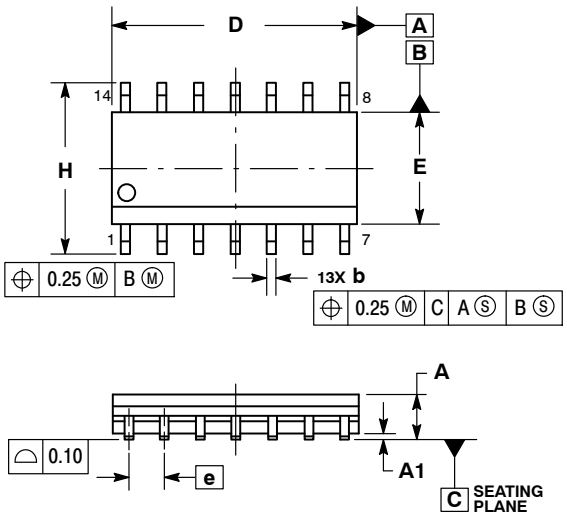
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

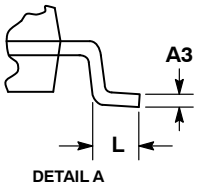


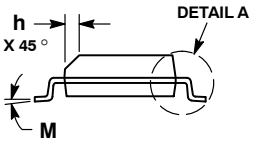
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



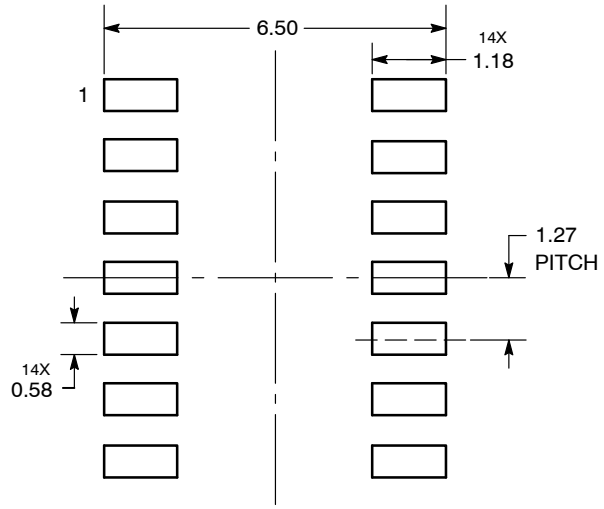




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

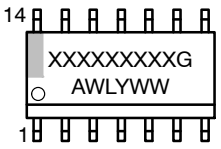
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42565B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOIC−14 NB**		**PAGE 1 OF 2**

SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

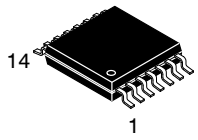
STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

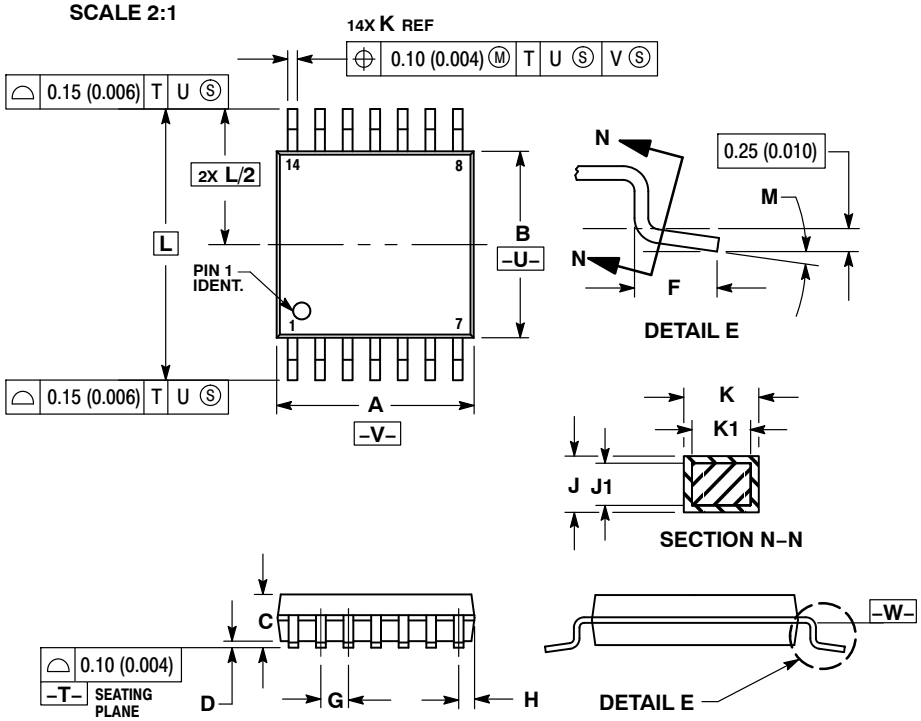
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016



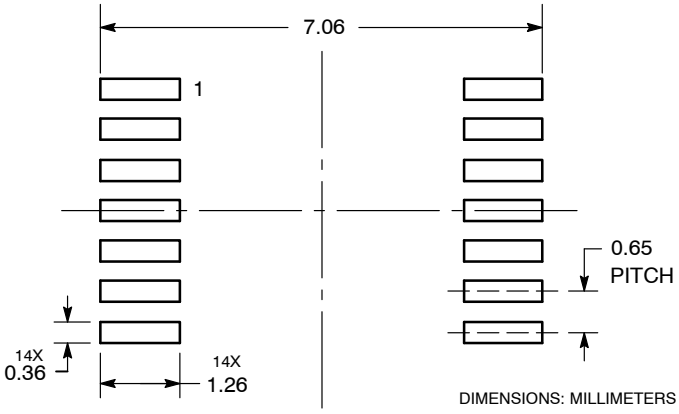
SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

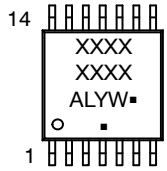
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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